

JAW EC-400																				Brian Lingg, PM			
Date	User	Film	Recipe	Substrate T	Thickness	Dep.time	Water center		Dep.rate	Stress	HF etch rate wafer	LPD (light point defects)	AVG dep.rate	AVG+10%	AVG-10%	AVG index@	AVG+2%	AVG-2%	AVG.Stress	AVG+10%	AVG-10%	Additional Notes	
				250 °C	(Å)	sec	Index @ 632.8nm	Index @ 1550nm	(nm/min)	MPa	(nm/min)	before dep.	after dep.										
1/1/2012	User	SIN	SIN_10	250 °C																		Deposition done on 4" Si wafer	
01/06/14	Bijjana	SIN	SIN_10	250	1055.25	568.1	1.949	1.899	11.15	571.87	78	547	11.19	12.31	10.07	1.937	1.976	1.899	508.86	610.63	407.09		
01/23/14	Bijjana	SIN	SIN_10	250	1133.40	568.1	1.935	1.890	11.97	446.98	90.66	137	377	11.19	12.31	10.07	1.937	1.976	1.899	508.86	610.63	407.09	1/23/14
02/03/14	Bijjana	SIN	SIN_10	250	1046.60	568.1	1.937	1.893	11.05	486.75	81.21	322	604	11.19	12.31	10.07	1.937	1.976	1.899	508.86	610.63	407.09	
02/19/14	Bijjana	SIN	SIN_10	250	1030.66	568.1	1.935	1.890	10.89	353.92	77.32	75	323	11.19	12.31	10.07	1.937	1.976	1.899	508.86	610.63	407.09	2/14/14 Silane change
03/14/14	Bijjana	SIN	SIN_10	250	1042.16	568.1	1.933	1.887	11.01	684.87	92.89	37	122	11.19	12.31	10.07	1.937	1.976	1.899	508.86	610.63	407.09	
04/08/14	Bijjana	SIN	SIN_10	250	1050.59	568.1	1.933	1.893	11.10		80.83			11.19	12.31	10.07	1.937	1.976	1.899	508.86	610.63	407.09	stress-wrong ID

Avg.Thickness	1059.78
Avg. Index	1.937
Avg+2%	1.976
Avg-2%	1.899
Avg Dep.Rate	11.19
Avg +10%	12.31
Avg -10%	10.07
Avg. Stress	508.86
Avg +20%	610.63
Avg -20%	407.09
Avg. HF e.r.	84.58

